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FDPF12N50UT

N-Channel UniFET™ Ultra FRFET™ MOSFET

500 V, 10 A, 800 mΩ

Features

- $R_{DS(on)} = 650 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 5 \text{ A}$
- Low Gate Charge (Typ. 21 nC)
- Low C_{rss} (Typ. 11 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant

Applications

- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. UniFET Ultra FRFET™ MOSFET has much superior body diode reverse recovery performance. Its t_{rr} is less than 50nsec and the reverse dv/dt immunity is 20V/nsec while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore UniFET Ultra FRFET MOSFET can remove additional component and improve system reliability in certain applications that require performance improvement of the MOSFET's body diode. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | FDPF12N50UT | Unit |
|----------------|--|--|------------------|
| V_{DSS} | Drain to Source Voltage | 500 | V |
| V_{GSS} | Gate to Source Voltage | ± 30 | V |
| I_D | Drain Current | - Continuous ($T_C = 25^\circ\text{C}$) | 10* |
| | | - Continuous ($T_C = 100^\circ\text{C}$) | 6* |
| I_{DM} | Drain Current | - Pulsed (Note 1) | 40* |
| E_{AS} | Single Pulsed Avalanche Energy | (Note 2) | 456 |
| I_{AR} | Avalanche Current | (Note 1) | 10 |
| E_{AR} | Repetitive Avalanche Energy | (Note 1) | 16.5 |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | 20 |
| P_D | Power Dissipation | ($T_C = 25^\circ\text{C}$) | 42 |
| | | - Derate Above 25°C | 0.3 |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to +150 | $^\circ\text{C}$ |
| T_L | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | 300 | $^\circ\text{C}$ |

*Drain current limited by maximum junction temperature.

Thermal Characteristics

| Symbol | Parameter | FDPF12N50UT | Unit |
|-----------------|---|-------------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. | 3.0 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient, Max. | 62.5 | |

Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|-------------|---------|----------------|-----------|------------|----------|
| FDPF12N50UT | FDPF12N50UT | TO-220F | Tube | N/A | N/A | 50 units |

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|-----------------|------|------|------|------|
|--------|-----------|-----------------|------|------|------|------|

Off Characteristics

| | | | | | | |
|--------------------------------|---|---|-----|-----|-----------|---------------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$, $T_J = 25^\circ\text{C}$ | 500 | - | - | V |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = 250 \mu\text{A}$, Referenced to 25°C | - | 0.7 | - | $\text{V}/^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 50 \text{ V}$, $V_{GS} = 0 \text{ V}$ | - | - | 25 | μA |
| | | $V_{DS} = 40 \text{ V}$, $T_C = 125^\circ\text{C}$ | - | - | 250 | |
| I_{GSS} | Gate to Body Leakage Current | $V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0 \text{ V}$ | - | - | ± 100 | nA |

On Characteristics

| | | | | | | |
|--------------|--------------------------------------|---|-----|------|-----|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$ | 3.0 | - | 5.0 | V |
| $R_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10 \text{ V}$, $I_D = 5 \text{ A}$ | - | 0.65 | 0.8 | Ω |
| g_{FS} | Forward Transconductance | $V_{DS} = 40 \text{ V}$, $I_D = 5 \text{ A}$ | - | 11 | - | S |

Dynamic Characteristics

| | | | | | | |
|--------------|-------------------------------|---|----------|------|------|----|
| C_{iss} | Input Capacitance | $V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$ | - | 1050 | 1395 | pF |
| C_{oss} | Output Capacitance | | - | 140 | 190 | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 11 | 17 | pF |
| $Q_{g(tot)}$ | Total Gate Charge at 10V | $V_{DS} = 40 \text{ V}$, $I_D = 10 \text{ A}$, $V_{GS} = 10 \text{ V}$ | - | 21 | 30 | nC |
| Q_{gs} | Gate to Source Gate Charge | | - | 6 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | (Note 4) | - | 9 | - |

Switching Characteristics

| | | | | | | |
|--------------|---------------------|--|----------|----|-----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 250 \text{ V}$, $I_D = 10 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_G = 25 \Omega$ | - | 35 | 80 | ns |
| t_r | Turn-On Rise Time | | - | 45 | 100 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | - | 60 | 130 | ns |
| t_f | Turn-Off Fall Time | | (Note 4) | - | 35 | 80 |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|--|---|---|-----|-----|---------------|
| I_S | Maximum Continuous Drain to Source Diode Forward Current | - | - | 10 | A | |
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | - | - | 40 | A | |
| V_{SD} | Drain to Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}$, $I_{SD} = 10 \text{ A}$ | - | - | 1.6 | V |
| t_{rr} | Reverse Recovery Time | $V_{GS} = 0 \text{ V}$, $I_{SD} = 10 \text{ A}$, $di_F/dt = 100 \text{ A}/\mu\text{s}$ | - | 65 | - | ns |
| Q_{rr} | Reverse Recovery Charge | | - | 0.1 | - | μC |

Notes:

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. $L = 9 \text{ mH}$, $I_{AS} = 10 \text{ A}$, $V_{DD} = 50 \text{ V}$, $R_G = 25 \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 10 \text{ A}$, $di/dt \leq 200 \text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

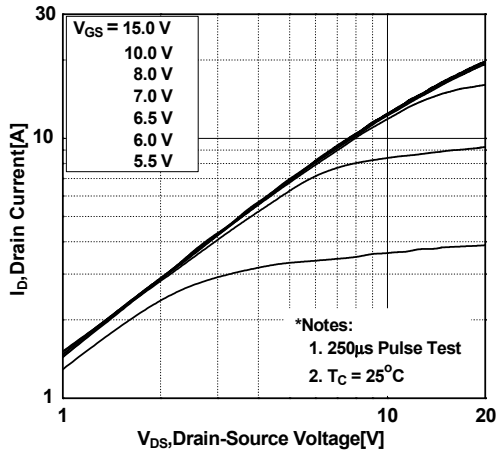


Figure 2. Transfer Characteristics

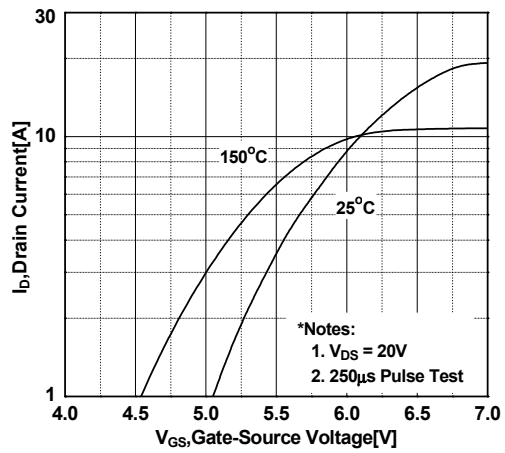


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

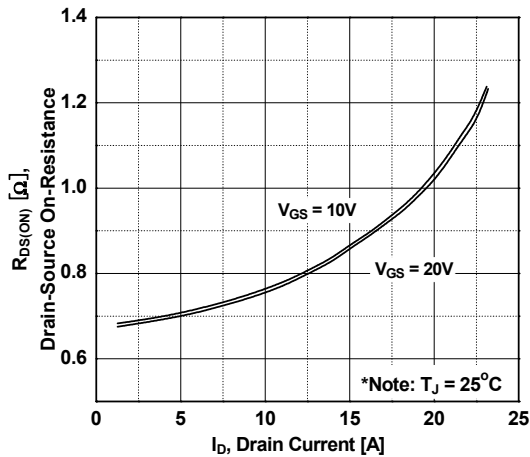


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

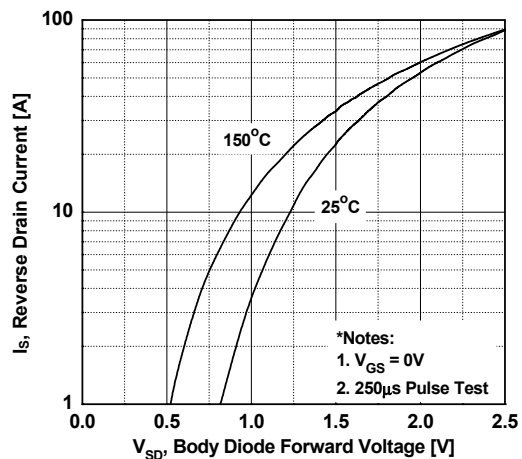


Figure 5. Capacitance Characteristics

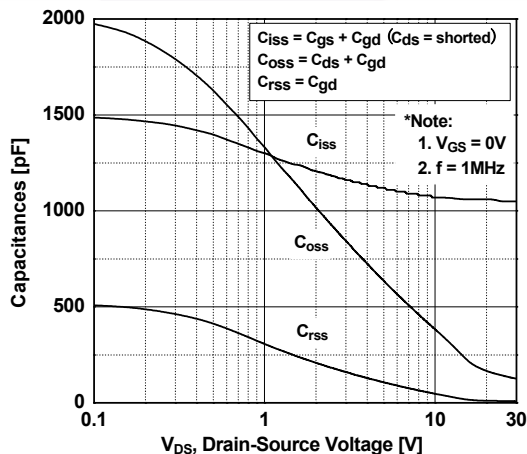
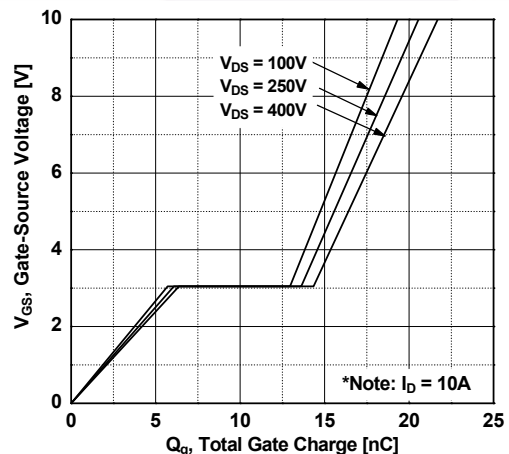


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

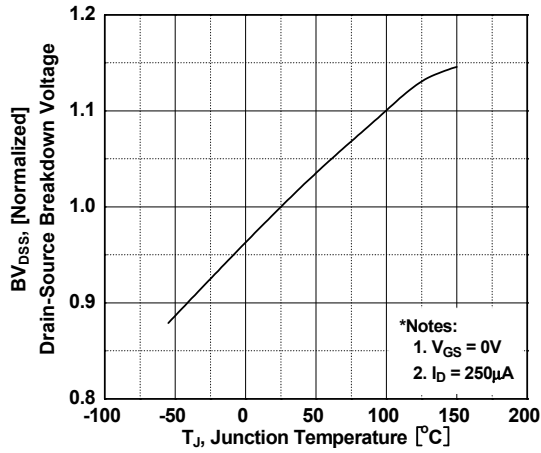


Figure 8. Maximum Safe Operating Area

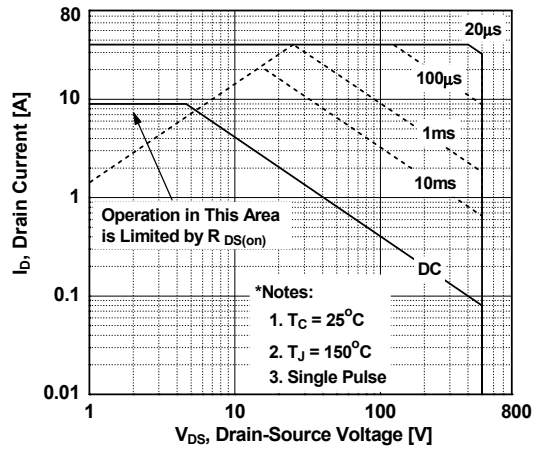


Figure 9. Maximum Drain Current vs. Case Temperature

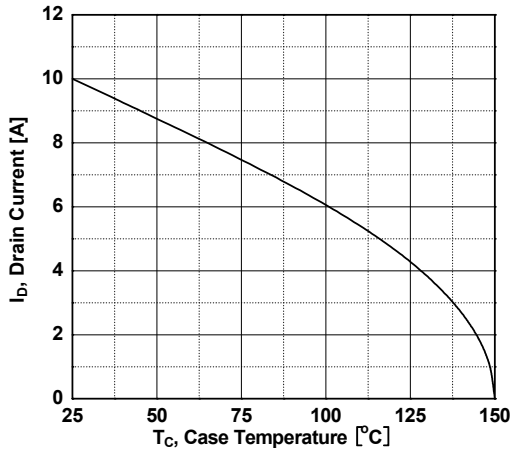


Figure 10. Transient Thermal Response Curve

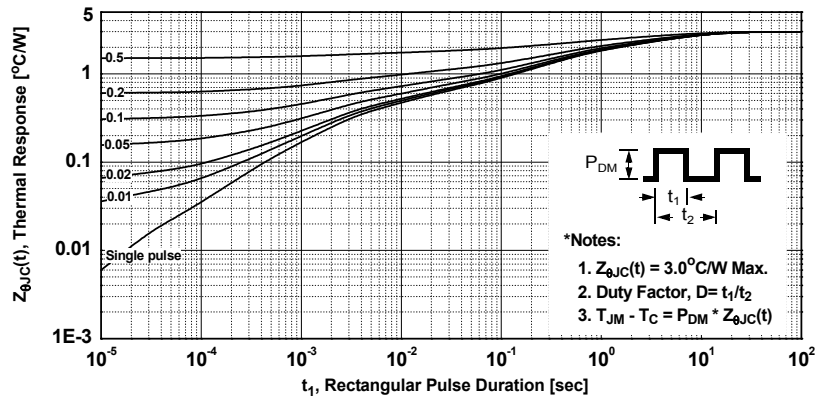




Figure 11. Gate Charge Test Circuit & Waveform



Figure 12. Resistive Switching Test Circuit & Waveforms



Figure 13. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 14. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3

Figure 15. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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